



EFS-SO1.001AUS

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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Hitoshi Shimizu, et al
App. No. : 09/918,018
Filed : July 30, 2001
For : SEMICONDUCTOR LASER DEVICE
HAVING LOWER THRESHOLD CURRENT
Examiner : Unknown
Group Art Unit : 2881

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7/16/03

(Date)

Mark J. Gallagher, Reg. No. 43,622

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing six (6) references that are also enclosed. This Information Disclosure Statement is being filed before the mailing date of a final action under 37 C.F.R. § 1.113 and before the mailing date of a Notice of Allowance under § 1.311. A certification under 37 C.F.R. § 1.97(e) is set forth below. Thus, no fee is required as set forth below in 37 C.F.R. § 1.97(c).

CERTIFICATION UNDER 37 C.F.R. § 1.97(e)(1)

I hereby certify that each item of information contained in this Statement was first cited in a communication from a foreign Patent Office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement.

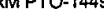
Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

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 <p>FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p>(USE SEVERAL SHEETS IF NECESSARY)</p>	<p>ATTY. DOCKET NO. FUSO1.001AUS</p>	<p>APPLICATION NO. 09/918,018</p>
<p>APPLICANT Hitoshi Shimizu <i>et al</i></p>		
<p>FILING DATE July 30, 2001</p>		<p>GROUP 2881</p>

U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	WO 00/38287	29.06.00	PCT				
	WO 01/33677 A2	10.05.01	WIPO				

EXAMINER
INITIAL

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

INITIAL	H. Shimizu et al., <i>1.2 um range GaInAs S QW lasers using Sb as surfactant</i> , ELECTRONICS LETTERS , Vol. 36, No. 16, August 3, 2000, 2 pages.
	X. Yang et al., <i>Molecular beam epitaxial growth of InGaAsN:Sb/GaAs quantum wells for long-wavelength semiconductor lasers</i> , Applied Physics Letters , Vol. 75, No. 2, July 12, 1999, pp. 178-180.
	X. Yang et al., <i>Photoluminescence of as-grown and thermally annealed InGaAsN/GaAs quantum wells grown by molecular beam epitaxy</i> , J. Vac. Sci. Technol. , Vol. B, No. 17(3), May/June 1999, pp. 1144-1146.
	X. Yang et al., <i>Low-Threshold 1.3-um InGaAsN:Sb-GaAs Single-Quantum-Well Lasers Grown by Molecular Beam Epitaxy</i> , IEEE PHOTONICS TECHNOLOGY LETTERS , Vol. 12, No. 2, February 2000, pp. 128-130.

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